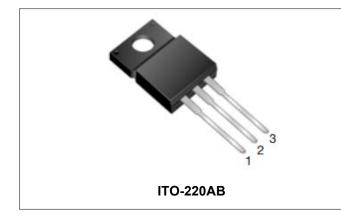


STF30H150C

Technical Data Data Sheet N1785, Rev. A



STF30H150C SCHOTTKY RECTIFIER



Circuit Diagram



Features

- 175 °C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	VRRM	-		
Working Peak Reverse Voltage	V _{RWM}		150	V
DC Blocking Voltage	VR			
Average Destified Featward Current		50% duty cycle @Tc=100°C,	15(Per Leg)	۸
Average Rectified Forward Current	IF (AV)	rectangular wave form	30(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	200	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per Leg)*	V _{F1}	@ 7.5A, Pulse, TJ = 25 °C @ 15A, Pulse, TJ = 25 °C	0.71 0.85	- 1.36	V
	V _{F2}	@ 7.5A, Pulse, TJ = 125 °C @ 15A, Pulse, TJ = 125 °C	0.60 0.71	- 0.79	V
Reverse Current(Per Leg)*	I _{R1}	$@V_R = rated V_{R,} T_J = 25 \ ^{\circ}C$	0.2	200	μA
	I _{R2}	$@V_R = rated V_R, T_J = 125 \circ C$	0.33	20	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz	485	-	рF
RSM Isolation Voltage(t = 1.0 second, R. H. < =30%, TA = 25 °C)	Viso	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction	-	4500	
		Clip mounting, the epoxy body is inside the heatsink.	-	3500	V
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

* Pulse width < 300 μs, duty cycle < 2%

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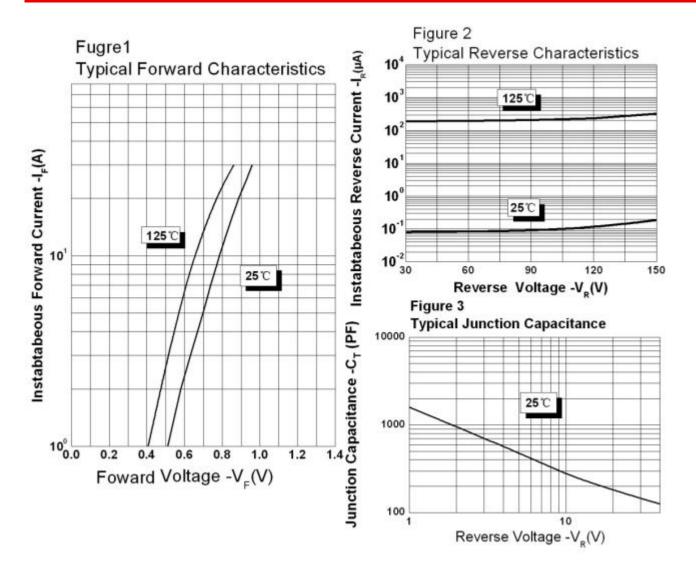
STF30H150C

RoHS 🗭

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R _{θJC}	DC operation	4.5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves



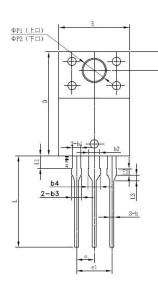


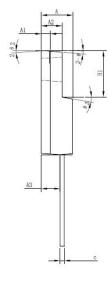
STF30H150C



Mechanical Dimensions ITO-220AB

-





OVMDOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
A	4.30	4.50	4.70	
A1	1.10	1.30	1.50	
A2	2.80	3.00	3.20	
A3	2.50	2.70	2.90	
b	0.50	0.60	0.75	
b1	1.10	1.20	1.35	
b2	1.50	1.60	1.75	
b3	1.20	1.30	1.45	
b4	1.60	1.70	1.85	
С	0.50	0.60	0.75	
D	14.80	15.00	15.20	
E	9.96	10.16	10.36	
e		2.55		
e1		5.10		
H1	6.50	6.70	6.90	
L	12.70	13.20	13.70	
L1	1.60	1.80	2.00	
L2	0.80	1.00	1.20	
L3	0.60	0.80	1.00	
ΦP1(上□)	3.30	3.50	3.70	
ΦΡ2 (下口)	2.99	3.19	3.39	
Q	2.50	2.70	2.90	
Θ1		5°		
Θ2		4°		
Θ3		10°		
Θ4		5°		
Θ5		5°		



Marking Diagram



Where XXXXX is YYWWL

ST	= Device Type
_	- Deekeen ture

- = Package type = Forward Current (30A)
- = Tj 175°C
- = Reverse Voltage (150V) 150
- = Configuration SSG
 - = SSG

F

30 Н

С

YY

L.

- = Year
- ŴŴ = Week
 - = Lot Number

Cautions: Molding resin Fnoxy resin LIL '94\/_0

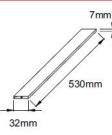
Ordering Information

Device	Package	Shipping
STF30H150C	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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Tube Specification



SMC DIDDE SOLUTIONS

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